

SANYO	No.4768	2SC4922
		NPN Epitaxial Planar Silicon Transistor

Muting Circuit, Driver Applications

Features

- High DC current gain.
- On-chip bias resistance (R1 = 47kΩ, R2 = 47kΩ)
- Very small-sized package permitting 2SC4922-applied sets to be made smaller and slimmer.
- Small ON resistance.

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector-to-Base Voltage	V _{CB0}	25	V
Collector-to-Emitter Voltage	V _{CEO}	20	V
Emitter-to-Base Voltage	V _{EBO}	10	V
Input Voltage	V _{IN}	18	V
Collector Current	I _C	100	mA
Collector Current (Pulse)	I _{CP}	200	mA
Base Current	I _B	20	mA
Collector Dissipation	P _C	150	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

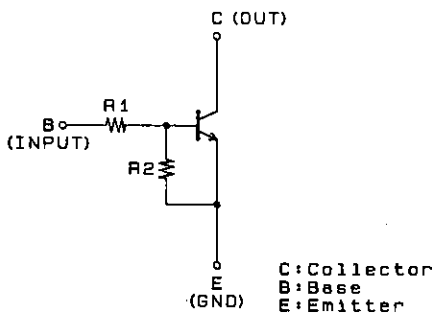
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = 20V, I _E = 0			0.1	μA
Collector Cutoff Current	I _{CEO}	V _{CE} = 15V, I _B = 0			0.5	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 5V, I _C = 0	30	53	80	μA
DC Current Gain	h _{FE}	V _{CE} = 2V, I _C = 5mA	200			
Gain-Bandwidth Product	f _T *	V _{CE} = 5V, I _C = 10mA		240		MHz
Output Capacitance	C _{ob} *	V _{CB} = 10V, f = 1MHz		1.4		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C = 2mA, I _B = 0.2mA		10	30	mV
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	25			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	20			V
Input OFF-State Voltage	V _{I(off)}	V _{CE} = 2V, I _C = 100μA	0.7	1.0	1.4	V
Input ON-State Voltage	V _{I(on)}	V _{CE} = 0.3V, I _C = 5mA	1.0	1.5	3.0	V
Input Resistance	R ₁		32	47	62	kΩ
Resistance Ratio	R _{1/R2}		0.9	1.0	1.1	
ON Resistance	R _{on}	V _{IN} = 10V, f = 1MHz		4.0		Ω

* Characteristic of the constituent transistor.

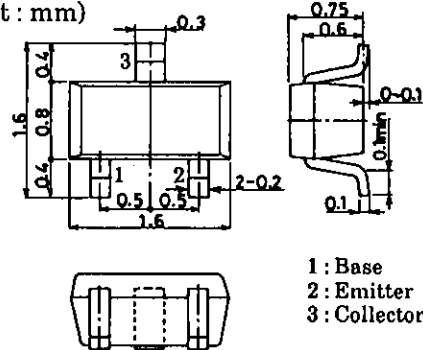
Marking: GA

Electrical Connection



Package Dimensions 2106A

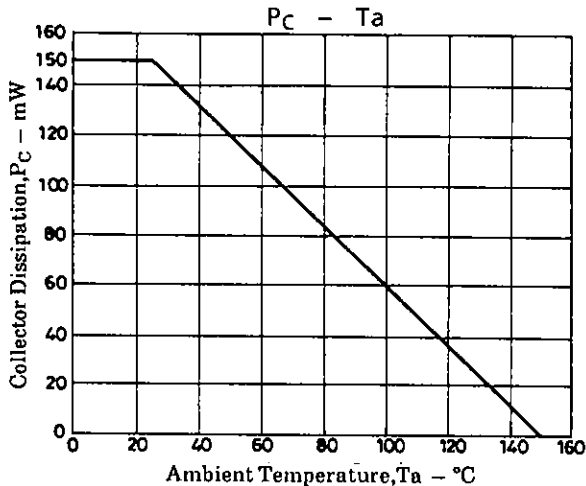
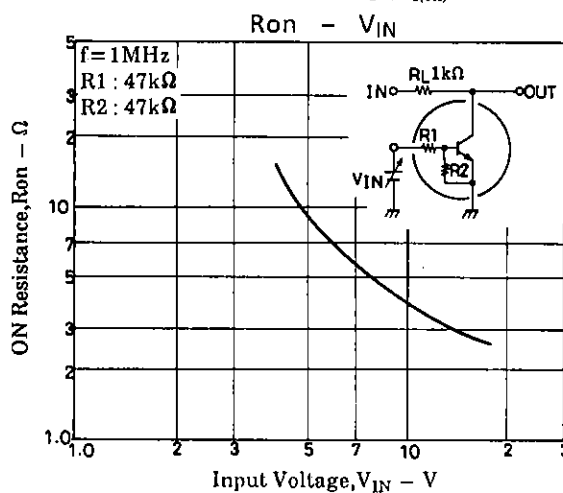
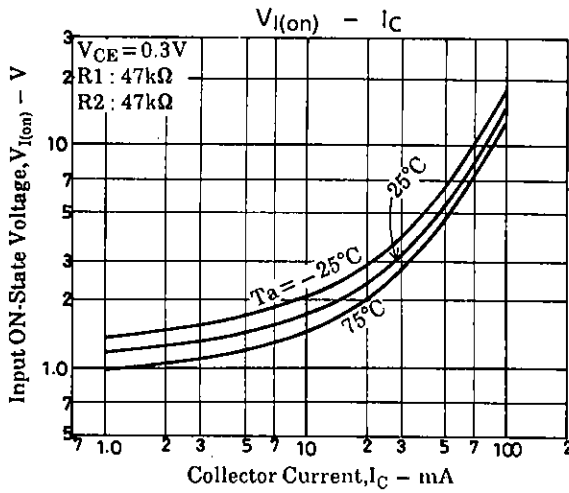
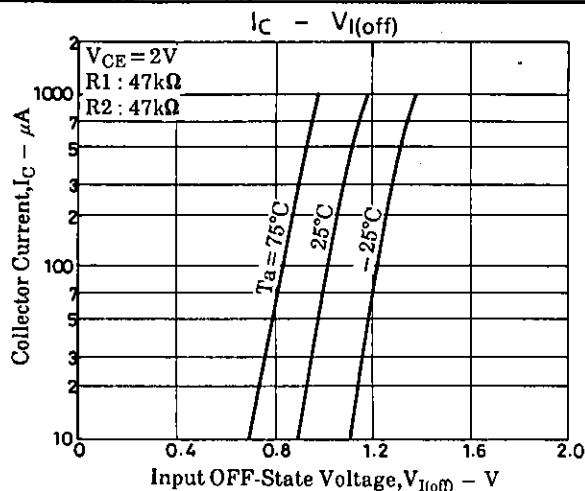
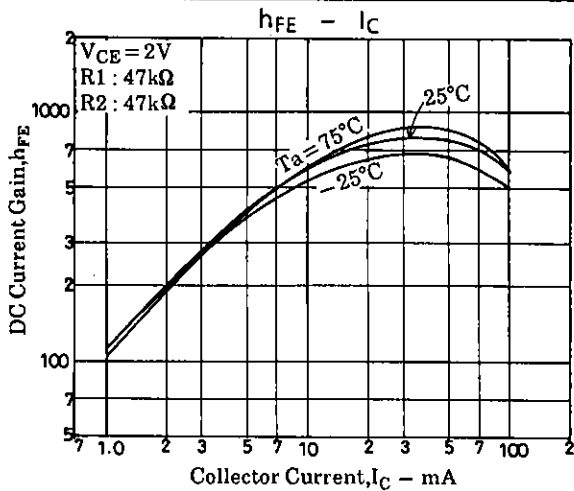
(unit: mm)



SANYO: SMCP

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